Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

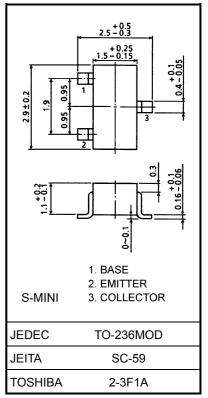
2SA1312

Audio Frequency Low Noise Amplifier Applications

- High voltage: $V_{CEO} = -120 \text{ V}$
- Excellent hFE linearity: hFE (IC = -0.1 mA)/ hFE (IC = -2 mA) h= 0.95 (typ.)
- High h_{FE} : $h_{FE} = 200 \sim 700$
- Low noise: NF (2) = 0.2dB (typ.), 3dB (max) at f = 1 kHz
- Complementary to 2SC3324
- Small package

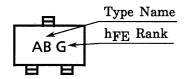
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-120	V
Collector-emitter voltage	V _{CEO}	-120	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-100	mA
Base current	Ι _Β	-20	mA
Collector power dissipation	P _C	150	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 0.012 g (typ.)

Marking



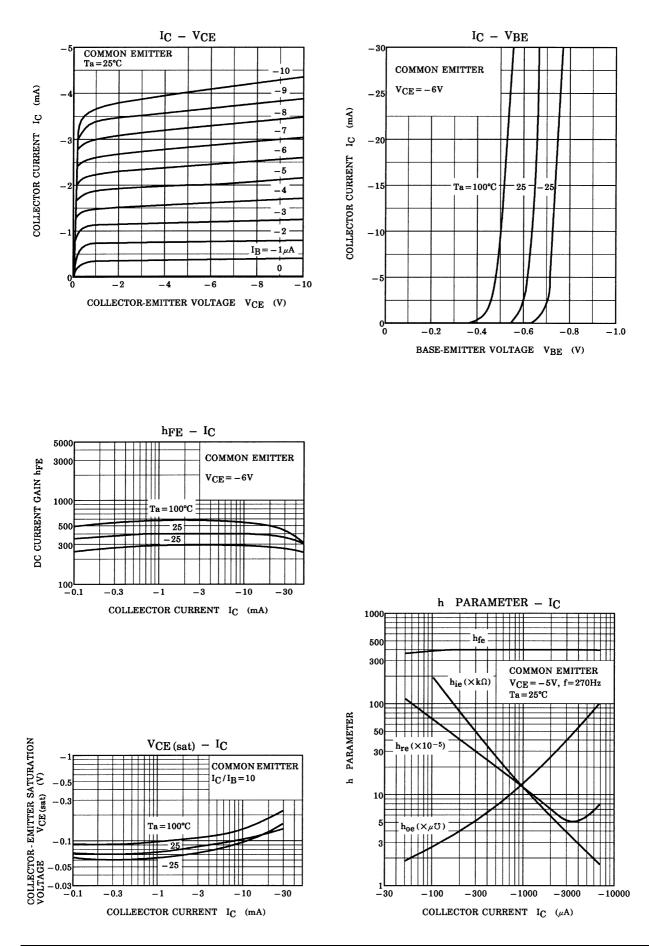
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I _{CBO}	$V_{CB} = -120 \text{ V}, \text{ I}_{E} = 0$			-0.1	μA	
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, \text{ I}_{C} = 0$	_	_	-0.1	μA	
DC current gain	h _{FE} (Note)	$V_{CE} = -6 V, I_C = -2 mA$	200	_	700		
Collector-emitter saturation voltage	V _{CE (sat)}	$I_{C} = -10 \text{ mA}, I_{B} = -1 \text{ mA}$	_	_	-0.3	V	
Transition frequency	f _T	$V_{CE} = -6 V, I_C = -1 mA$	_	100	—	MHz	
Collector output capacitance	C _{ob}	$V_{CB} = -10 V$, $I_E = 0$, $f = 1 MHz$	_	4	—	pF	
Noise figure	NF (1)	V_{CE} = –6 V, I_C = –0.1 mA, f = 100 Hz, Rg = 10 k Ω	—	0.5	6	dB	
	NF (2)	V_{CE} = -6 V, I_C = -0.1 mA, f = 1 kHz, Rg = 10 k Ω		0.2	3	UD	

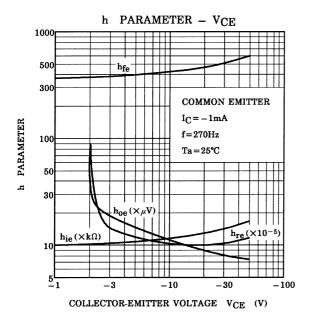
Note: hFE classification GR (G): 200~400, BL (L): 350~700

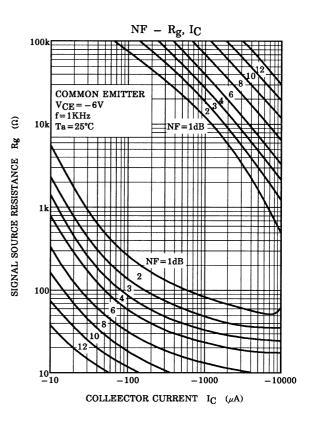
() marking symbol

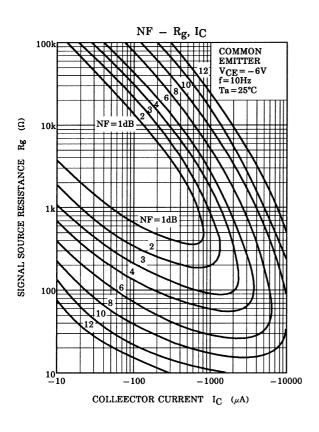
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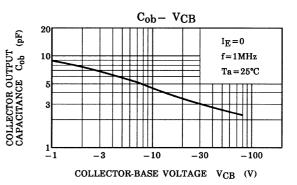


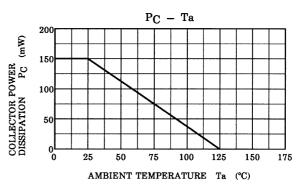
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